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GROUP 1700

In re Patent Application of  
David C. Ahlgren et al.

Serial No.: 09/633,857

Group Art Unit: 1765

Filed: August 7, 2000

Examiner: R. Kunemund

For: IN-SITU MONITORING AND CONTROL OF GERMANIUM  
PROFILE IN SILICON-GERMANIUM ALLOY FILMS AND  
TEMPERATURE MONITORING DURING DEPOSITION OF  
SILICON FILMS

#17c  
519103  
mw

Commissioner for Patents  
United States Patent and Trademark Office  
P. O. Box 1450  
Alexandria, Virginia 22313-1450

## AMENDMENT UNDER 37 C. F. R. §1.111

Sir:

In response to the Office Action mailed February  
7, 2003, please amend the above-identified application  
as follows:

In the Specification:

Please substitute the following paragraphs for the  
corresponding paragraphs beginning at the indicated  
location in the specification as originally filed. A  
marked up copy of these paragraphs showing currently  
requested changes is attached as an Appendix to this  
response.

Page 16, line 19+:

Thus, if during the calibration period, the  
germane mass flow rate can be accurately known, the  
percentage of germanium being deposited in a SiGe film  
in the actual (e.g. production) process sequence can be  
known from the rate of hydrogen evolution at any given